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(54) Title: POLYSILICON LINERS

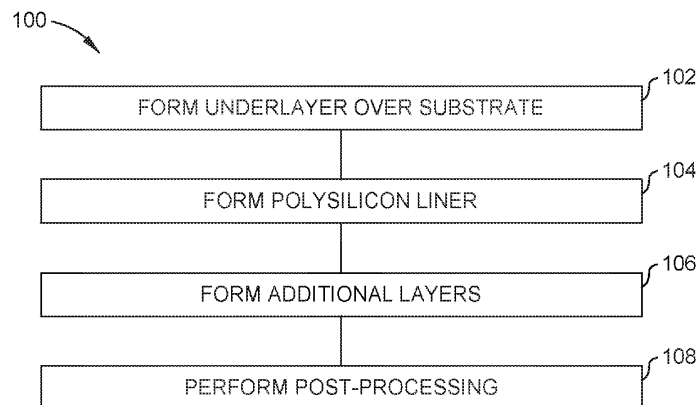


FIG. 1

(57) Abstract: Aspects of the disclosure provide a method including depositing an underlayer comprising silicon oxide over a substrate, depositing a polysilicon liner on the underlayer, and depositing an amorphous silicon layer on the polysilicon liner. Aspects of the disclosure provide a device intermediate including a substrate, an underlayer comprising silicon oxide formed over the substrate, a polysilicon liner disposed on the underlayer, and an amorphous silicon layer disposed on the polysilicon liner.

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